

PMBD914

Single high-speed switching diode Rev. 06 — 11 February 2009

Product data sheet

Product profile

1.1 General description

Single high-speed switching diode, fabricated in planar technology, and encapsulated in a small Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview**

Type number[1]	Package	
	NXP	JEDEC
PMBD914	SOT23	TO-236AB
PMBD914/DG		

^{[1] /}DG: halogen-free

1.2 Features

- High switching speed: t_{rr} ≤ 4 ns
- Low leakage current
- Repetitive peak reverse voltage: $V_{RRM} \le 100 \text{ V}$
- Low capacitance: C_d ≤ 1.5 pF
- Reverse voltage: V_R ≤ 100 V
- Small SMD plastic package

1.3 Applications

High-speed switching

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current		<u>[1]</u> -	-	215	mA
V_R	reverse voltage		-	-	100	V
t _{rr}	reverse recovery time		[2] _	-	4	ns

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



^[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

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2. Pinning information

Table 3. Pinning

	J		
Pin	Description	Simplified outline	Graphic symbol
1	anode		
2	not connected		3
3	cathode	1 2	1 1 2 006aaa764

3. Ordering information

Table 4. Ordering information

Type number[1]	Package		
	Name	Description	Version
PMBD914	-	plastic surface-mounted package; 3 leads	SOT23
PMBD914/DG			

^{[1] /}DG: halogen-free

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
PMBD914	*5D
PMBD914/DG	YB*

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	100	V
V_R	reverse voltage		-	100	V
I _F	forward current		<u>[1]</u> _	215	mA
I _{FRM}	repetitive peak forward current		-	500	mA
I _{FSM}	non-repetitive peak forward	square wave	[2]		
	current	$t_p = 1 \mu s$	-	4	Α
		$t_p = 1 \text{ ms}$	-	1	Α
		t _p = 1 s	-	0.5	Α

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^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

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Table 6. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P_{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1][3]	250	mW
T _j	junction temperature		-	150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	500	K/W
R _{th(j-t)}	thermal resistance from junction to tie-point		[2] _	-	330	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Daramatar					
Parameter	Conditions	Min	Тур	Max	Unit
forward voltage	$I_F = 1 \text{ mA}$	-	-	715	mV
	I _F = 10 mA	-	-	855	mV
	$I_F = 50 \text{ mA}$	-	-	1	V
	I _F = 150 mA	-	-	1.25	V
reverse current	V _R = 25 V	-	-	25	nA
	V _R = 75 V	-	-	1	μΑ
	$V_R = 25 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	30	μΑ
	$V_R = 75 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μΑ
diode capacitance	$f = 1 MHz; V_R = 0 V$	-	-	1.5	pF
reverse recovery time		<u>[1]</u> _	-	4	ns
forward recovery voltage		[2] _	-	1.75	V
	forward voltage reverse current diode capacitance reverse recovery time	forward voltage $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 50 \text{ mA}$ $I_F = 150 \text{ mA}$ $I_F = 150 \text{ mA}$ $V_R = 25 \text{ V}$ $V_R = 75 \text{ V}$ $V_R = 25 \text{ V}; T_j = 150 \text{ °C}$ $V_R = 75 \text{ V}; T_j = 150 \text{ °C}$ diode capacitance $f = 1 \text{ MHz}; V_R = 0 \text{ V}$			

^[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

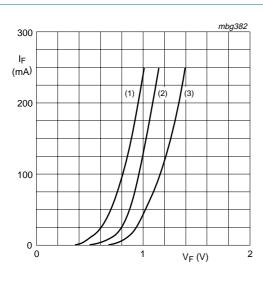
^[2] $T_i = 25$ °C prior to surge.

^[3] Soldering point of cathode tab.

^[2] Soldering point of cathode tab.

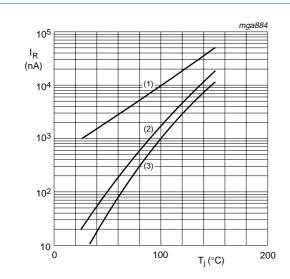
^[2] When switched from $I_F = 10$ mA; $t_r = 20$ ns.

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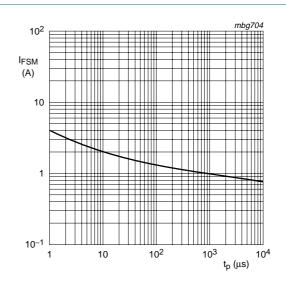
- (1) $T_{amb} = 150 \,^{\circ}C$; typical values
- (2) $T_{amb} = 25 \,^{\circ}C$; typical values
- (3) $T_{amb} = 25 \,^{\circ}C$; maximum values

Fig 1. Forward current as a function of forward voltage



- (1) $V_R = 75 \text{ V}$; maximum values
- (2) V_R = 75 V; typical values
- (3) $V_R = 25 \text{ V}$; typical values

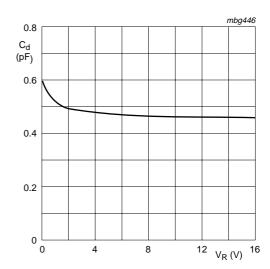
Fig 3. Reverse current as a function of junction temperature



Based on square wave currents.

 $T_j = 25$ °C; prior to surge

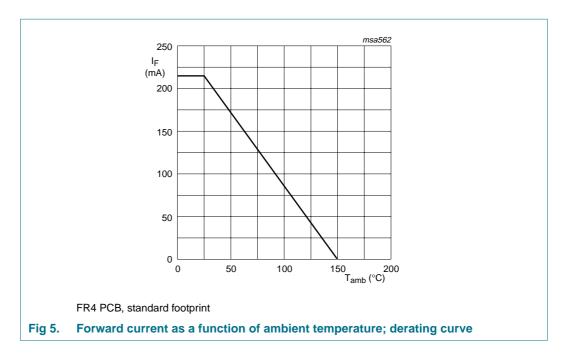
Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values



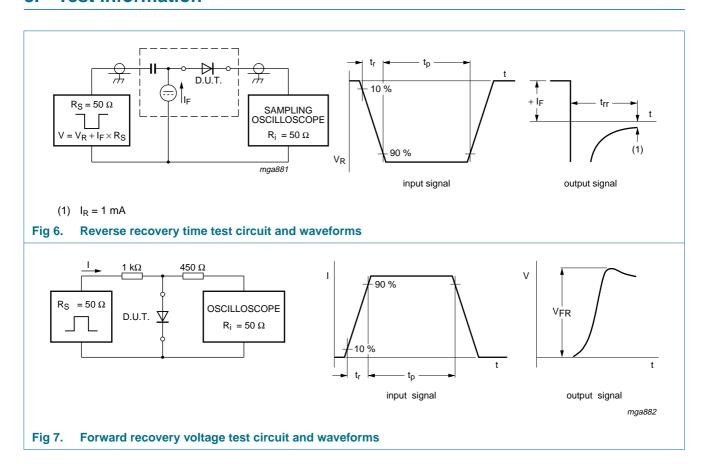
 $f = 1 \text{ MHz}; T_{amb} = 25 \,^{\circ}\text{C}$

Fig 4. Diode capacitance as a function of reverse voltage; typical values

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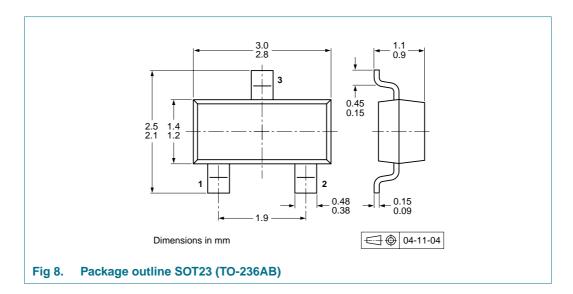


8. Test information



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9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

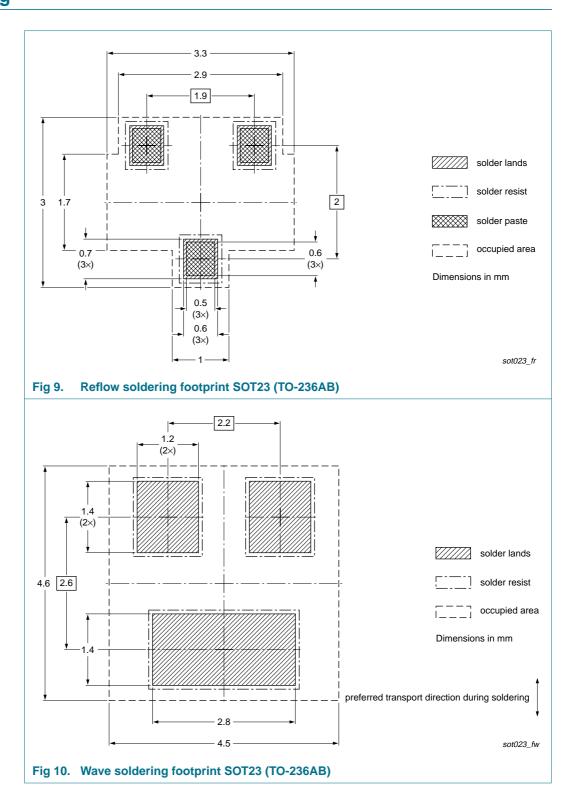
Type number[2] Package		Description	Packing	Packing quantity	
			3000	10000	
PMBD914	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235	
PMBD914/DG					

^[1] For further information and the availability of packing methods, see Section 14.

^{[2] /}DG: halogen-free

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11. Soldering



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12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBD914_6	20090211	Product data sheet	-	PMBD914_5
Modifications:	• •	PMBD914/DG added egal information": updated		
PMBD914_5	20071126	Product data sheet	-	PMBD914_4
PMBD914_4	20040106	Product specification	-	PMBD914_3
PMBD914_3	19990511	Product specification	-	PMBD914_2
PMBD914_2	19960918	Product specification	-	PMBD914_1
PMBD914_1	19960404	Product specification	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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